SWITCHMODE™ Power Rectifiers

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 10 A Total
- Pb-Free Packages are Available*

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B Machine Model C

*For additional information on our Pb-Free strategy and soldering details, please

download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

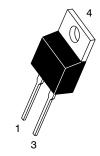


ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIERS 10 AMPERES 35 to 45 VOLTS





MARKING DIAGRAM

AY WWG B10x5 KA

A = Assembly Location

TO-220AC

CASE 221B

PLASTIC

Y = Year
WW = Work Week
G = Pb-Free Package
B10x5 = Device Code
x = 3 or 4
KA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR1035	TO-220	50 Units/Rail
MBR1035G	TO-220 (Pb-Free)	50 Units/Rail
MBR1045	TO-220	50 Units/Rail
MBR1045G	TO-220 (Pb-Free)	50 Units/Rail

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage			V
DC Blocking Voltage MBR1035 MBR1045	V _R	35 45	
Average Rectified Forward Current (T _C = 135°C, Per Device)	I _{F(AV)}	10	Α
Peak Repetitive Forward Current, (Square Wave, 20 kHz, T _C = 135°C)	I _{FRM}	10	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	Α
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	1.0	Α
Storage Temperature Range		-65 to +175	°C
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Voltage Rate of Change (Rated V _R)		10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	60	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2)	VF	- - -	0.55 0.67 0.78	0.57 0.72 0.84	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, Tj = 125°C) (Rated dc Voltage, Tj = 25°C)	i _R	-	5.3 0.008	15 0.1	mA

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

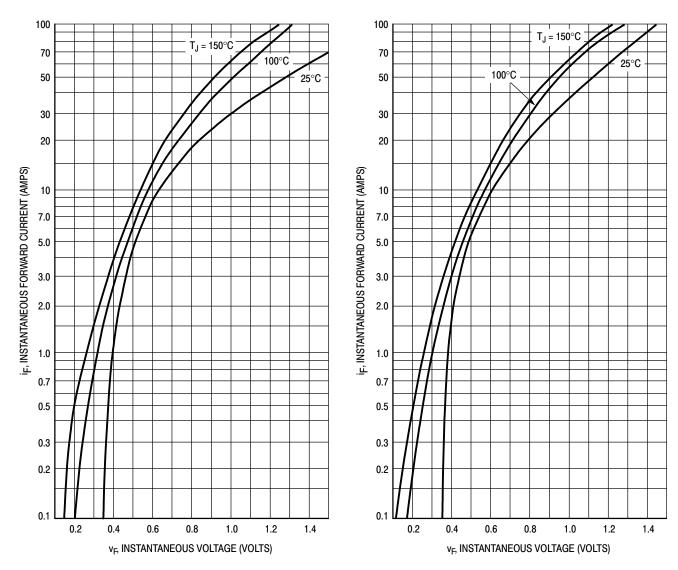


Figure 1. Maximum Forward Voltage

Figure 2. Typical Forward Voltage

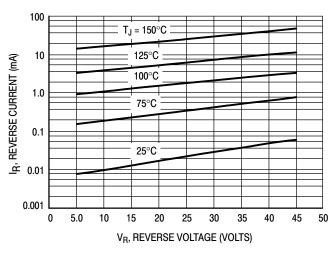
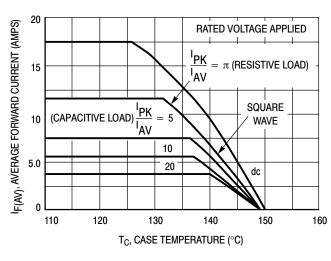


Figure 3. Maximum Reverse Current

Figure 4. Maximum Surge Capability



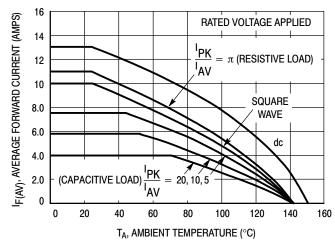
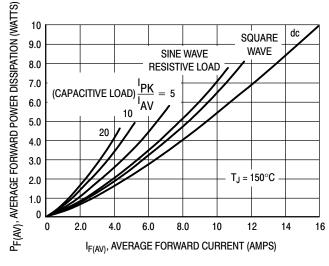


Figure 5. Current Derating, Infinite Heatsink





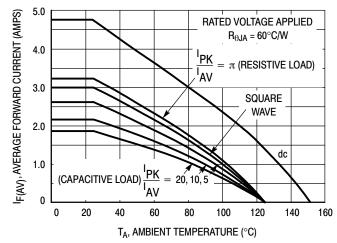


Figure 7. Forward Power Dissipation

Figure 8. Current Derating, Free Air

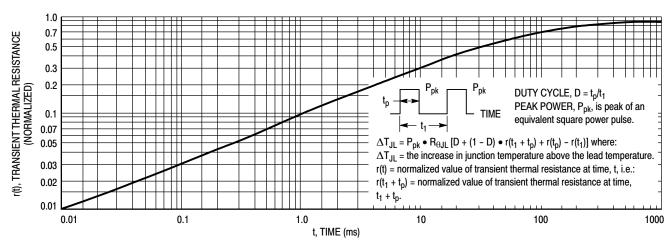


Figure 9. Thermal Response

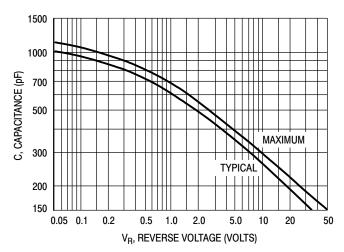
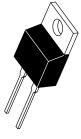


Figure 10. Capacitance

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS





TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

Q SCALE 1:1

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE 4. CATHODE

PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

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